

# FQP4P40

## 400V P-Channel MOSFET

### General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp ballast based on complimentary half bridge.

### Features

- -3.5A, -400V,  $R_{DS(on)} = 3.1\Omega$  @  $V_{GS} = -10$  V
- Low gate charge ( typical 18 nC)
- Low  $C_{SS}$  ( typical 11 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	FQP4P40	Units
$V_{DSS}$	Drain-Source Voltage	-400	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	-3.5	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	-2.2	A
$I_{DM}$	Drain Current - Pulsed	(Note 1)	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	85	W
	- Derate above $25^\circ\text{C}$	0.68	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.47	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

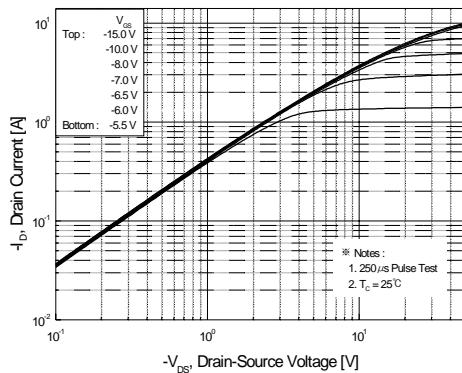
**Elerical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = -250 \mu\text{A}$	-400	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.36	--	$\text{V}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = -400 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{\text{DS}} = -320 \text{ V}$ , $T_C = 125^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{\text{GSSF}}$	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = -30 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
$I_{\text{GSSR}}$	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = 30 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
<b>On Characteristics</b>						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = -250 \mu\text{A}$	-3.0	--	-5.0	V
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = -10 \text{ V}$ , $I_D = -1.75 \text{ A}$	--	2.44	3.1	$\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = -50 \text{ V}$ , $I_D = -1.75 \text{ A}$ (Note 4)	--	2.7	--	S
<b>Dynamic Characteristics</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = -25 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$	--	520	680	pF
$C_{\text{oss}}$	Output Capacitance		--	80	105	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	11	15	pF
<b>Switching Characteristics</b>						
$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = -200 \text{ V}$ , $I_D = -3.5 \text{ A}$ , $R_G = 25 \Omega$	--	13	35	ns
$t_r$	Turn-On Rise Time		--	55	120	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	35	80	ns
$t_f$	Turn-Off Fall Time		--	37	85	ns
$Q_g$	Total Gate Charge		--	18	23	nC
$Q_{\text{gs}}$	Gate-Source Charge	$V_{\text{DS}} = -320 \text{ V}$ , $I_D = -3.5 \text{ A}$ , $V_{\text{GS}} = -10 \text{ V}$	--	3.8	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	9.4	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	-3.5	A	
$I_{\text{SM}}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-14	A	
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = -3.5 \text{ A}$	--	--	-5.0	V
$t_{\text{rr}}$	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = -3.5 \text{ A}$ , $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	260	--	ns
$Q_{\text{rr}}$	Reverse Recovery Charge		--	1.4	--	$\mu\text{C}$

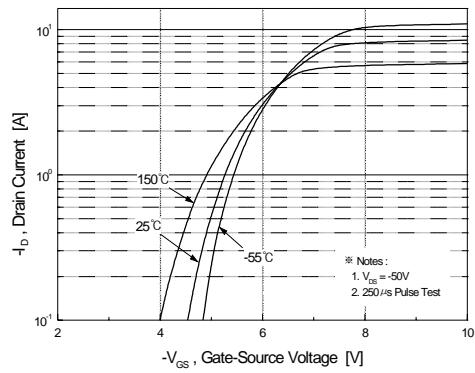
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 37mH,  $I_{AS} = -3.5\text{A}$ ,  $V_{DD} = -50\text{V}$ ,  $R_G = 25 \Omega$ . Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -3.5\text{A}$ ,  $dI/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq \text{BV}_{\text{DSS}}$ . Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

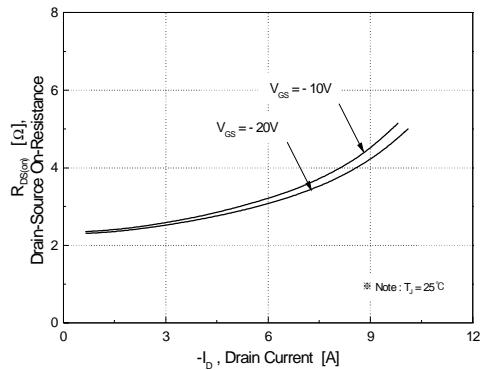
## Typical Characteristics



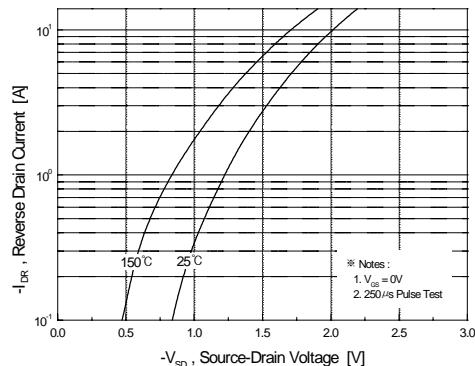
**Figure 1. On-Region Characteristics**



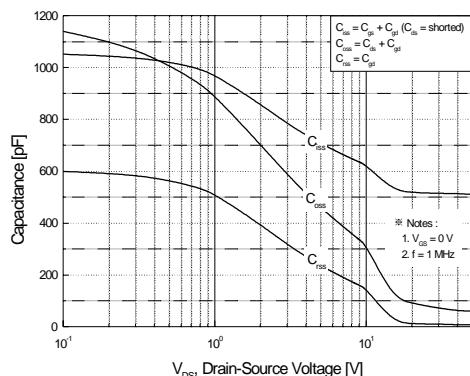
**Figure 2. Transfer Characteristics**



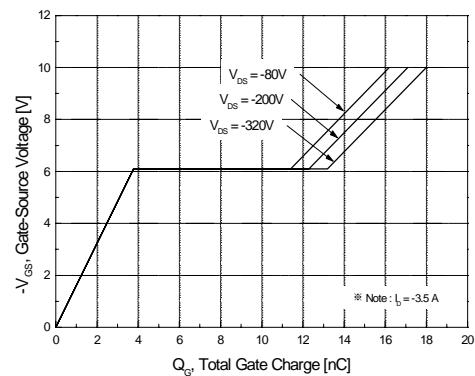
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**